

**isc Silicon NPN Power Transistor**

**2SC2073**

**DESCRIPTION**

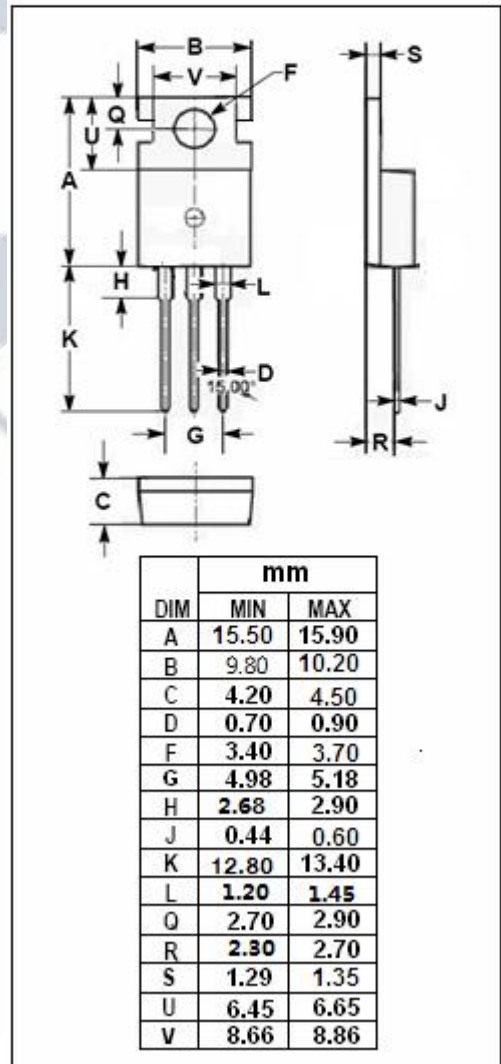
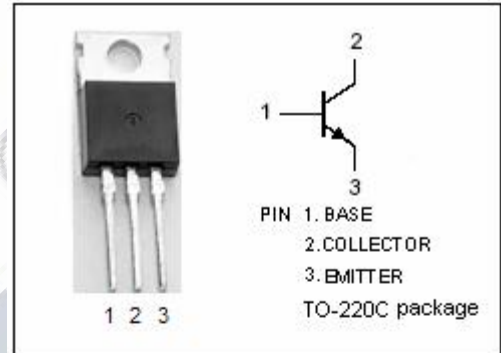
- Collector-Emitter Breakdown Voltage-  
:V<sub>(BR)CEO</sub>= 150V(Min)
- Wide Area of Safe Operation
- Complement to Type 2SA940
- 100% tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

**APPLICATIONS**

- Power amplifier applications.
- Vertical output applications.

**ABSOLUTE MAXIMUM RATINGS(T<sub>a</sub>=25°C)**

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	150	V
V <sub>CEO</sub>	Collector-Emitter Voltage	150	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current-Continuous	1.5	A
I <sub>B</sub>	Base Current-Continuous	0.5	A
P <sub>C</sub>	Collector Power Dissipation @ T <sub>a</sub> =25°C	1.5	W
	Collector Power Dissipation @ T <sub>C</sub> =25°C	25	
T <sub>J</sub>	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-55~150	°C



**isc Silicon NPN Power Transistor****2SC2073****ELECTRICAL CHARACTERISTICS****T<sub>c</sub>=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 500mA; I <sub>B</sub> = 50mA			1.5	V
V <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 500mA ; V <sub>CE</sub> = 10V			0.85	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 120V ; I <sub>E</sub> = 0			10	μ A
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 5V; I <sub>C</sub> = 0			10	μ A
h <sub>FE</sub>	DC Current Gain	I <sub>C</sub> = 500mA ; V <sub>CE</sub> = 10V	40		140	
C <sub>OB</sub>	Output Capacitance	I <sub>E</sub> = 0; V <sub>CB</sub> = 10V; f <sub>test</sub> = 1MHz		35		pF
f <sub>T</sub>	Current-Gain—Bandwidth Product	I <sub>C</sub> = 500mA; V <sub>CE</sub> = 10V		4		MHz